

ELECTRONIC COMPONENT, METHOD FOR MAKING, AND TARGET
THEREFOR

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Abstract of the Disclosure

A dielectric material (43, 61, 63, 71) is formed using $\text{Ba}(\text{Ti}_{(1-x)}\text{Sn}_x)\text{O}_3$.
The dielectric material (43, 61, 63, 71) can be formed using a metal organic
decomposition or solution-gelation process or by sputtering material from
10 a sputtering target (12).

(FIG. 1 to accompany abstract)